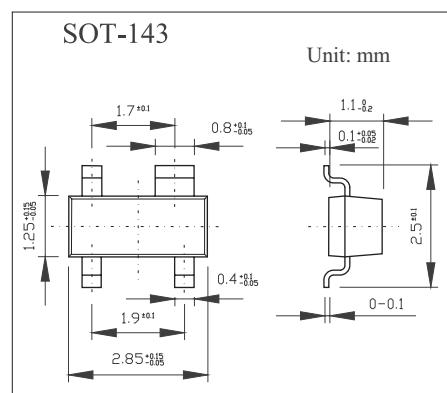


Schottky Barrier (Double) Diodes**BAS40-07****■ Features**

- Low forward voltage
- Guard ring protected
- Small plastic SMD package
- Low diode capacitance.

**■ Absolute Maximum Ratings Ta = 25°C**

Parameter	Symbol	Test Condition	MIN	MAX	Unit
continuous reverse voltage	V _R			40	V
continuous forward current	I _F			120	mA
repetitive peak forward current	I _{FRM}	t _p ≤ 1 s; δ ≤ 0.5		120	mA
non-repetitive peak forward current	I _{FSM}	t _p < 10 ms		200	A
storage temperature	T _{stg}		-65	+150	°C
junction temperature	T _j			150	°C
operating ambient temperature	T _{amb}		-65	+150	°C
thermal resistance from junction to ambient	R _{th j-a}			500	K/W

BAS40-07**■ Electrical Characteristics Ta = 25°C**

Parameter	Symbol	Test Condition	Min	Max	Unit
forward voltage	V _F	I _F = 1 mA		380	mV
		I _F = 10 mA		500	mV
		I _F = 40 mA		1	V
reverse current	I _R	V _R = 30 V; note 1		1	nA
		V _R = 40 V; note 1		10	µ A
diode capacitance	C _d	f = 1 MHz; V _R = 0		5	pF

Note

1. Pulse test: t_P = 300 ms; δ = 0.02.**■ Marking**

Marking	47
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